9. (New) A method of manufacturing semiconductor components, the method comprising:

introducing depressions into a wafer of a first conductivity type;

coating both sides of the wafer with doping atoms;

carrying out a diffusion process;

dicing the wafer into individual chips so that, in an internal area, each of the chips has at least one depression; and

sawing the depressions.

10. (New) The method according to claim 9, wherein the depressions are formed as pits having a rectangular cross section.

11. (New) The method according to claim 9, further comprising applying metal layers to both sides of the wafer before the wafer is diced.

12. (New) The method according to claim 9, wherein the wafer is diced in areas of the wafer where no depressions have been introduced.

13. (New) The method according to claim 9, further comprising covering a top side of the wafer using a dopant of a second conductivity type.

14. (New) The method according to claim 9, further comprising covering a bottom side of the wafer using a dopant of the first conductivity type.

15. (New) The method according to claim 9, further comprising applying metal layers to first and third layers.

16. (New) A semiconductor component comprising:

a first layer of a first conductivity type having a top side and a bottom side, the first layer having areas of different thickness due to at least one depression introduced into the top side;